

CMOSH2-4L
SURFACE MOUNT
HIGH CURRENT, LOW V_F
SILICON SCHOTTKY DIODE



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMOSH2-4L is a high current, low V_F silicon Schottky diode in an SOD-523 surface mount package. This device offers a V_F as low as 0.33 volts and is designed for small signal general purpose applications where size and low loss is required.

MARKING CODE: 4L

ULTRAmini™



SOD-523 CASE

MAXIMUM RATINGS: (T_A=25°C)

Peak Repetitive Reverse Voltage	V _{RRM}	40	V
Continuous Forward Current	I _F	200	mA
Peak Repetitive Forward Current	I _{FRM}	350	mA
Peak Forward Surge Current, tp=10ms	I _{FSM}	1.0	A
Power Dissipation	P _D	250	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	500	°C/W

SYMBOL

UNITS

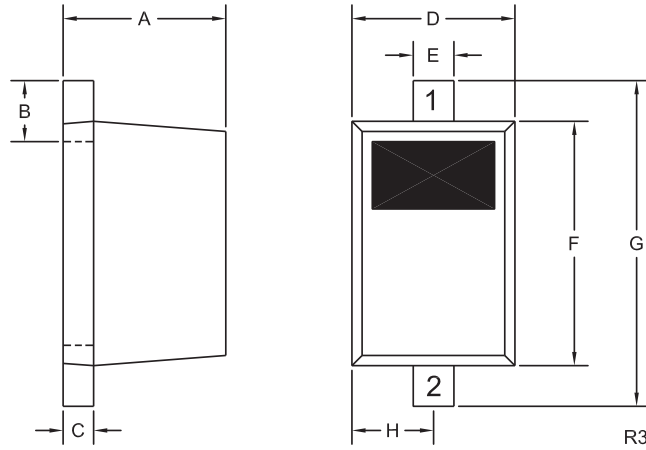
ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _R	V _R =20V		11	50	μA
BV _R	I _R =100μA	40	53		V
V _F	I _F =10mA		0.24	0.325	V
V _F	I _F =100mA		0.35	0.4	V
V _F	I _F =200mA		0.42	0.5	V
C _T	V _R =4.0V, f=1.0MHz		8.5	10	pF
t _{rr}	I _F =I _R =10mA, I _{rr} =1.0mA, R _L =100Ω		4.0	5.0	ns

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SOD-523 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Cathode
- 2) Anode

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DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.020	0.031	0.50	0.80
B	0.008	0.016	0.20	0.40
C	0.002	0.008	0.05	0.20
D	0.028	0.035	0.70	0.90
E	0.008	0.014	0.20	0.35
F	0.039	0.055	1.00	1.40
G	0.055	0.071	1.40	1.80
H	0.016		0.40	

SOD-523 (REV: R3)

R5 (11-April 2011)